IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming ~~an amorphous~~ a first semiconductor film comprising amorphous semiconductor over an insulating surface;

introducing a metallic element for promoting crystallization of the ~~amorphous~~ first semiconductor film comprising amorphous semiconductor into the ~~amorphous~~ first semiconductor film comprising amorphous semiconductor;

partially crystallizing the ~~amorphous~~ first semiconductor film by a heat treatment to form a ~~polycrystalline~~ second semiconductor film in which ~~a~~ crystal ~~region~~ regions and ~~an~~ amorphous ~~region~~ regions are intermingled; and

performing a laser annealing to the ~~polycrystalline~~ second semiconductor film with a laser beam having a wave length from 360 to 650 nm in order for the crystal regions generated by the heat treatment to remain and for annealing mainly the amorphous regions.

2. (Withdrawn) A method of manufacturing a semiconductor device, comprising:

a first step of introducing a metallic element for promoting crystallization of an amorphous semiconductor film introducing into the amorphous semiconductor film;

a second step of partially crystallizing the amorphous semiconductor film by heat treatment to form a first polycrystalline semiconductor film; and

a third step of irradiating a laser beam with a wave length from 360 to 650 nm to the

first polycrystalline semiconductor film to form a second polycrystalline semiconductor film,

wherein the first polycrystalline semiconductor film is crystallized in the range from 92 to 99% in a region which becomes an active layer of a TFT.

3. (Withdrawn) A method of manufacturing a semiconductor device, comprising:

a first step of introducing a metallic element for promoting crystallization of an amorphous semiconductor film introducing into the amorphous semiconductor film;

a second step of partially crystallizing the amorphous semiconductor film by heat treatment to form a first polycrystalline semiconductor film; and

a third step of irradiating a laser beam with a wave length from 360 to 650 nm to the first polycrystalline semiconductor film to form a second polycrystalline semiconductor film,

wherein, in the first polycrystalline semiconductor film, the total area of amorphous regions in a region which becomes an active layer of a TFT is set from 1 to 8% of an area of the region which becomes the active layer of the TFT.

4. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming a first semiconductor film comprising amorphous semiconductor over an insulating surface;

introducing a metallic element for promoting crystallization of the first semiconductor film comprising amorphous semiconductor into the first semiconductor film comprising amorphous semiconductor;

partially crystallizing the first semiconductor film comprising amorphous

semiconductor by a heat treatment to form a second semiconductor film ~~comprising polycrystalline semiconductor~~ in which crystal regions and amorphous regions are intermingled; and

irradiating a laser beam with a wave length from 360 to 650 nm to the second semiconductor film ~~comprising polycrystalline semiconductor~~ in which the crystal regions and the amorphous regions are intermingled to form a third semiconductor film comprising ~~a~~ polycrystalline semiconductor ~~film~~ with an improved crystallinity in order for the crystal regions generated by the heat treatment to remain and for annealing mainly the amorphous regions;

wherein an area of each of the amorphous regions in the second semiconductor film ~~comprising polycrystalline semiconductor~~ in which the crystal regions and the amorphous regions are intermingled is equal to or less than 10.0 μm^2, and

wherein an area of at least one of the amorphous regions is equal to or greater than 0.30 μm^2.

5. (Withdrawn) A method of manufacturing a semiconductor device according to claim 1, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

6. (Withdrawn) A method of manufacturing a semiconductor device according to claim 2, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

7. (Withdrawn) A method of manufacturing a semiconductor device according to claim 3, wherein the metallic element is one kind or plural kinds of elements selected from the group

consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

8. (Original) A method of manufacturing a semiconductor device according to claim 4, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

9. (Withdrawn) A method of manufacturing a semiconductor device according to claim 1, wherein the laser beam is one kind selected from the group consisting of a second harmonic of a YAG laser, a second harmonic of a glass laser, an Ar laser, a second harmonic of a YLF laser, and a second harmonic of a YVO_4 laser.

10. (Withdrawn) A method of manufacturing a semiconductor device according to claim 2, wherein the laser beam is one kind selected from the group consisting of a second harmonic of a YAG laser, a second harmonic of a glass laser, an Ar laser, a second harmonic of a YLF laser, and a second harmonic of a YVO_4 laser.

11. (Withdrawn) A method of manufacturing a semiconductor device according to claim 3, wherein the laser beam is one kind selected from the group consisting of a second harmonic of a YAG laser, a second harmonic of a glass laser, an Ar laser, a second harmonic of a YLF laser, and a second harmonic of a YVO_4 laser.

12. (Original) A method of manufacturing a semiconductor device according to claim 4, wherein the laser beam is one kind selected from the group consisting of a second harmonic of a

YAG laser, a second harmonic of a glass laser, an Ar laser, a second harmonic of a YLF laser, and a second harmonic of a YVO_4 laser.

13. (Withdrawn) A method of manufacturing a semiconductor device according to claim 1, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

14. (Withdrawn) A method of manufacturing a semiconductor device according to claim 2, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

15. (Withdrawn) A method of manufacturing a semiconductor device according to claim 3, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

16. (Original) A method of manufacturing a semiconductor device according to claim 4, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

17. (Withdrawn) A method of manufacturing a semiconductor device according to claim 1, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

18. (Withdrawn) A method of manufacturing a semiconductor device according to claim 2, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a

portable information terminal.

19. (Withdrawn) A method of manufacturing a semiconductor device according to claim 3, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

20. (Original) A method of manufacturing a semiconductor device according to claim 4, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

21. (Withdrawn) A method of manufacturing a semiconductor device according to claim 1, wherein the laser beam has a wave length from 400 to 600 nm.

22. (Withdrawn) A method of manufacturing a semiconductor device according to claim 2, wherein the laser beam has a wave length from 400 to 600 nm.

23. (Withdrawn) A method of manufacturing a semiconductor device according to claim 3, wherein the laser beam has a wave length from 400 to 600 nm.

24. (Original) A method of manufacturing a semiconductor device according to claim 4, wherein the laser beam has a wave length from 400 to 600 nm.

25. (Withdrawn) A method of manufacturing a semiconductor device according to claim 2, wherein the first polycrystalline semiconductor film is crystallized in the range from 92 to 99% in a region which becomes an active layer of a TFT.

26. (Withdrawn) A method of manufacturing a semiconductor device according to claim 3, wherein, in the first polycrystalline semiconductor film, the total area of amorphous regions in a region which becomes an active layer of a TFT is set from 1 to 6% of an area of the region which becomes the active layer of the TFT.

27. (Withdrawn) A method of manufacturing a semiconductor device according to claim 2, wherein the second polycrystalline semiconductor film formed is crystallized in equal to or greater than 99% of the region which becomes the active layer of the TFT.

28. (Withdrawn) A method of manufacturing a semiconductor device according to claim 3, wherein, in the second polycrystalline semiconductor film, the total area of amorphous regions in the region which becomes the active layer of the TFT is set equal to or less than 1% of the area of the region which becomes the active layer of the TFT.

29. (Withdrawn) A semiconductor device comprising a semiconductor film, wherein:

a metallic element for promoting crystallization of an amorphous semiconductor film is introduced into the amorphous semiconductor film;

a first polycrystalline semiconductor film is formed by heat treatment, in which 92 to

99% of a region which becomes an active layer of a TFT is crystallized; and

a second polycrystalline semiconductor film formed by irradiating a laser beam with a wave length from 360 to 650 nm to the first polycrystalline semiconductor film is used as the active layer of the TFT.

30. (Withdrawn) A semiconductor device comprising a semiconductor film, wherein:

a metallic element for promoting crystallization of an amorphous semiconductor film is introduced into the amorphous semiconductor film;

a first polycrystalline semiconductor film is formed by heat treatment, in which a total area of amorphous regions in a region which becomes an active layer of a TFT is set from 1 to 8% of an area of the region which becomes the active layer of the TFT; and

a second polycrystalline semiconductor film formed by irradiating a laser beam with a wave length from 360 to 650 nm to the first polycrystalline semiconductor film is used as the active layer of the TFT.

31. (Withdrawn) A semiconductor device comprising a semiconductor film, wherein:

a metallic element for promoting crystallization of an amorphous semiconductor film is introduced into the amorphous semiconductor film;

a first polycrystalline semiconductor film is formed by heat treatment, in which a area of each of the amorphous regions in a region which becomes an active layer of a TFT is equal to or less than 10.0 μm^2 and an area of at least one amorphous region is equal to or greater than 0.30 μm^2; and

a second polycrystalline semiconductor film formed by irradiating a laser beam with a

wave length from 360 to 650 nm to the first polycrystalline semiconductor film is used as the active layer of the TFT.

32. (Withdrawn) A semiconductor device comprising: a semiconductor film; a gate insulating film; and a gate electrode formed on an insulating surface,

wherein the semiconductor film is a second polycrystalline semiconductor film formed by a method comprising the steps of:

introducing a metallic element for promoting crystallization of an amorphous semiconductor film into the amorphous semiconductor film;

forming a first polycrystalline semiconductor film by heat treatment, in which 92 to 99% of a region which becomes an active layer of a TFT is crystallized; and

irradiating a laser beam with a wave length from 360 to 650 nm to the first polycrystalline semiconductor film to form the second polycrystalline semiconductor film.

33. (Withdrawn) A semiconductor device comprising: a semiconductor film; a gate insulating film; and a gate electrode formed on an insulating surface,

wherein the semiconductor film is a second polycrystalline semiconductor film formed by a method comprising the steps of:

introducing a metallic element for promoting crystallization of an amorphous semiconductor film into the amorphous semiconductor film;

forming a first polycrystalline semiconductor film by heat treatment, in which a total area of amorphous regions in a region which becomes an active layer of a TFT is set from 1 to 8% of a area of the region which becomes the active layer of the TFT; and

irradiating a laser beam with a wave length from 360 to 650 nm to the first polycrystalline semiconductor film to form the second polycrystalline semiconductor film.

34. (Withdrawn) A semiconductor device comprising: a semiconductor film; a gate insulating film; and a gate electrode formed on an insulating surface,

wherein the semiconductor film is a second polycrystalline semiconductor film, which is obtained by introducing a metallic element for promoting crystallization of an amorphous semiconductor film into the amorphous semiconductor film, and irradiating a laser beam to a first polycrystalline semiconductor film which is obtained by partially crystallizing with heat treatment;

wherein an area of each of the amorphous regions in a region of the first polycrystalline semiconductor film is equal to or less than 10.0 μm^2;

wherein an area of at least one of the amorphous regions has is equal to or greater than 0.30 μm^2; and

wherein the wave length of the laser beam is from 360 to 650 nm.

35. (Currently Amended) A semiconductor device according to ~~any of~~ claim 29, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

36. (Currently Amended) A semiconductor device according to ~~any of~~ claim 30, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

37. (Currently Amended) A semiconductor device according to ~~any of~~ claim 31, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

38. (Currently Amended) A semiconductor device according to ~~any of~~ claim 32, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

39. (Currently Amended) A semiconductor device according to ~~any of~~ claim 33, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

40. (Currently Amended) A semiconductor device according to ~~any of~~ claim 34, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

41. (Currently Amended) A semiconductor device according to claim 29, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

42. (Currently Amended) A semiconductor device according to claim 30, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

43. (Currently Amended) A semiconductor device according to claim 31, wherein the

semiconductor device is a liquid crystal display device or a light-emitting device.

44. (Currently Amended) A semiconductor device according to claim 32, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

45. (Currently Amended) A semiconductor device according to claim 33, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

46. (Currently Amended) A semiconductor device according to claim 34, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

47. (Currently Amended) A semiconductor device according to claim 29, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

48. (Currently Amended) A semiconductor device according to claim 30, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

49. (Currently Amended) A semiconductor device according to claim 31, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle

type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

50. (Currently Amended) A semiconductor device according to claim 32, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

51. (Currently Amended) A semiconductor device according to claim 33, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

52. (Currently Amended) A semiconductor device according to claim 32, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

53. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming ~~an amorphous~~ a first semiconductor film comprising amorphous semiconductor over an insulating surface;

introducing a metallic element for promoting crystallization of the ~~amorphous~~ first

semiconductor film comprising amorphous semiconductor into the ~~amorphous~~ first semiconductor film comprising amorphous semiconductor;

partially crystallizing the ~~amorphous~~ first semiconductor film comprising amorphous semiconductor by a heat treatment to form a ~~polycrystalline~~ second semiconductor film in which ~~a~~ crystal ~~region~~ regions and ~~an~~ amorphous ~~region~~ regions are intermingled; and

performing a laser annealing to the ~~polycrystalline~~ second semiconductor film in which the crystal regions and the amorphous regions are intermingled with a laser beam having a wave length from 360 to 650 nm in order for the crystal regions generated by the heat treatment to remain and for annealing mainly the amorphous regions to form a third semiconductor film comprising polycrystalline semiconductor;

forming a gate insulating film over the ~~polycrystalline~~ third semiconductor film comprising polycrystalline semiconductor after the step of performing the laser annealing; and

forming a gate electrode over the gate insulating film.

54. (Currently Amended) A semiconductor device according to ~~any of~~ claim 53, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

55. (Previously Presented) A method of manufacturing a semiconductor device according to claim 53, wherein the laser beam is one kind selected from the group consisting of a second harmonic of a YAG laser, a second harmonic of a glass laser, an Ar laser, a second harmonic of a YLF laser, and a second harmonic of a YVO_4 laser.

56. (Previously Presented) A method of manufacturing a semiconductor device according to claim 53, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or a portable information terminal.

57. (Previously Presented) A method of manufacturing a semiconductor device according to claim 53, wherein the laser beam has a wave length from 400 to 600 nm.

58. (Currently Amended) A semiconductor device according to claim 53, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.

59. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming a first semiconductor film comprising amorphous semiconductor over an insulating surface;

introducing a metallic element for promoting crystallization of the first semiconductor film comprising amorphous semiconductor into the first semiconductor film comprising amorphous semiconductor;

partially crystallizing the first semiconductor film comprising amorphous semiconductor by a heat treatment to form a second semiconductor film ~~comprising polycrystalline semiconductor~~ in which crystal regions and amorphous regions are intermingled;

irradiating a laser beam with a wave length from 360 to 650 nm to the second semiconductor film in which the crystal regions and the amorphous regions are intermingled to form

a third semiconductor film comprising ~~a~~ polycrystalline semiconductor ~~film~~ with an improved crystallinity in order for the crystal regions generated by the heat treatment to remain and for annealing mainly the amorphous regions;

forming a gate insulating film over the third semiconductor film; and

forming a gate electrode over the gate insulating film,

wherein an area of each of the amorphous regions in the second semiconductor film ~~comprising polycrystalline semiconductor~~ in which the crystal regions and the amorphous regions are intermingled is equal to or less than 10.0 μm^2, and

wherein an area of at least one of the amorphous regions is equal to or greater than 0.30 μm^2.

60. (Currently Amended) A semiconductor device according to ~~any of~~ claim 59, wherein the metallic element is one kind or plural kinds of elements selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As and Sb.

61. (Previously Presented) A method of manufacturing a semiconductor device according to claim 59, wherein the laser beam is one kind selected from the group consisting of a second harmonic of a YAG laser, a second harmonic of a glass laser, an Ar laser, a second harmonic of a YLF laser, and a second harmonic of a YVO_4 laser.

62. (Previously Presented) A method of manufacturing a semiconductor device according to claim 59, wherein the semiconductor device is a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, or

a portable information terminal.

63. (Previously Presented) A method of manufacturing a semiconductor device according to claim 59, wherein the laser beam has a wave length from 400 to 600 nm.

64. (Currently Amended) A semiconductor device according to claim 59, wherein the semiconductor device is a liquid crystal display device or a light-emitting device.